

Tu-Pei Chen

List of Publications by Year in descending order

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341
papers

7,238
citations

70961

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85405

71
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all docs

344
docs citations

344
times ranked

8482
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Epilepsy detection with artificial neural network based on as-fabricated neuromorphic chip platform. AIP Advances, 2022, 12, 035106. | 0.6 | 3 |
| 2 | Transparent electronic and photoelectric synaptic transistors based on the combination of an InGaZnO channel and a TaO _x gate dielectric. Nanoscale, 2022, 14, 10245-10254. | 2.8 | 8 |
| 3 | Stock Price Prediction Based on an Energy-Efficient Spiking-LSTM Hardware Accelerator. Journal of Physics: Conference Series, 2021, 1828, 012050. | 0.3 | 0 |
| 4 | Performance Enhancement of Transparent Amorphous IGZO Thin-Film Transistor Realized by Sputtered Amorphous AlO _x Passivation Layer. ECS Journal of Solid State Science and Technology, 2021, 10, 045006. | 0.9 | 5 |
| 5 | Design of a constant loop bandwidth phase-locked loop based on artificial neural network. IEICE Electronics Express, 2021, 18, 20210120-20210120. | 0.3 | 0 |
| 6 | Quantized STDP-based online-learning spiking neural network. Neural Computing and Applications, 2021, 33, 12317-12332. | 3.2 | 17 |
| 7 | Efficient and reconfigurable reservoir computing to realize alphabet pronunciation recognition based on processing-in-memory. Applied Physics Letters, 2021, 119, . | 1.5 | 4 |
| 8 | A Large-Size HfO ₂ Based RRAM Structure Suitable for Integration of One RRAM with One InGaZnO Thin Film Transistor for Large-Area Applications. ECS Journal of Solid State Science and Technology, 2021, 10, 115004. | 0.9 | 1 |
| 9 | Application of Deep Compression Technique in Spiking Neural Network Chip. IEEE Transactions on Biomedical Circuits and Systems, 2020, 14, 274-282. | 2.7 | 10 |
| 10 | Uncovering the Indium Filament Revolution in Transparent Bipolar ITO/SiO _x /ITO Resistive Switching Memories. ACS Applied Materials & Interfaces, 2020, 12, 4579-4585. | 4.0 | 17 |
| 11 | 3D Geometric Engineering of the Double Wedge-Like Electrodes for Filament-Type RRAM Device Performance Improvement. IEEE Access, 2020, 8, 4924-4934. | 2.6 | 2 |
| 12 | Investigation of Electrical Noise Signal Triggered Resistive Switching and Its Implications. IEEE Transactions on Electron Devices, 2020, 67, 4178-4184. | 1.6 | 5 |
| 13 | HfO _x -Based RRAM Device With Sandwich-Like Electrode for Thermal Budget Requirement. IEEE Transactions on Electron Devices, 2020, 67, 4193-4200. | 1.6 | 16 |
| 14 | Design of AM Self-Capacitive Transparent Touch Panel Based on a-IGZO Thin-Film Transistors. IEEE Access, 2020, 8, 76929-76934. | 2.6 | 6 |
| 15 | STBNN: Hardware-friendly spatio-temporal binary neural network with high pattern recognition accuracy. Neurocomputing, 2020, 409, 351-360. | 3.5 | 19 |
| 16 | An energy-efficient deep convolutional neural networks coprocessor for multi-object detection. Microelectronics Journal, 2020, 98, 104737. | 1.1 | 8 |
| 17 | Spike-driven gated recurrent neural network processor for electrocardiogram arrhythmias detection realised in 55-nm CMOS technology. Electronics Letters, 2020, 56, 1230-1232. | 0.5 | 7 |
| 18 | A Neuromorphic-Hardware Oriented Bio-Plausible Online-Learning Spiking Neural Network Model. IEEE Access, 2019, 7, 71730-71740. | 2.6 | 18 |

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 19 | Uniform and electroforming-free resistive memory devices based on solution-processed triple-layered NiO/Al ₂ O ₃ thin films. Applied Physics A: Materials Science and Processing, 2019, 125, 1. | 1.1 | 4 |
| 20 | Study of Recall Time of Associative Memory in a Memristive Hopfield Neural Network. IEEE Access, 2019, 7, 58876-58882. | 2.6 | 11 |
| 21 | Design of a Neural Network-Based VCO With High Linearity and Wide Tuning Range. IEEE Access, 2019, 7, 60120-60125. | 2.6 | 7 |
| 22 | Selective Scattering of Blue and Red Light Based on Silver and Gold Nanocubes. ECS Journal of Solid State Science and Technology, 2019, 8, R51-R57. | 0.9 | 2 |
| 23 | Implementation of a Low Noise Amplifier With Self-Recovery Capability. IEEE Access, 2019, 7, 43076-43083. | 2.6 | 4 |
| 24 | Surface modification of Na ₂ Ti ₃ O ₇ nanofibre arrays using N-doped graphene quantum dots as advanced anodes for sodium-ion batteries with ultra-stable and high-rate capability. Journal of Materials Chemistry A, 2019, 7, 12751-12762. | 5.2 | 83 |
| 25 | Winner-takes-all mechanism realized by memristive neural network. Applied Physics Letters, 2019, 115, . | 1.5 | 15 |
| 26 | Low energy consumption dual-ion electrochemical deionization system using NaTi ₂ (PO ₄) ₃ -AgNPs electrodes. Desalination, 2019, 451, 241-247. | 4.0 | 99 |
| 27 | Sharp selective scattering of red, green, and blue light achieved via gain material's loss compensation. Optics Express, 2019, 27, 9189. | 1.7 | 4 |
| 28 | Toward transparent projection display: recent progress in frequency-selective scattering of RGB light based on metallic nanoparticle's localized surface plasmon resonance. Opto-Electronic Advances, 2019, 2, 19002001-19002015. | 6.4 | 11 |
| 29 | Resonant scattering of green light enabled by Ag@TiO ₂ and its application in a green light projection screen. Nanoscale, 2018, 10, 2438-2446. | 2.8 | 11 |
| 30 | 3D hierarchical defect-rich NiMo ₃ S ₄ nanosheet arrays grown on carbon textiles for high-performance sodium-ion batteries and hydrogen evolution reaction. Nano Energy, 2018, 49, 460-470. | 8.2 | 107 |
| 31 | Bifunctional porous iron phosphide/carbon nanostructure enabled high-performance sodium-ion battery and hydrogen evolution reaction. Energy Storage Materials, 2018, 15, 98-107. | 9.5 | 102 |
| 32 | Predicting House Price With a Memristor-Based Artificial Neural Network. IEEE Access, 2018, 6, 16523-16528. | 2.6 | 39 |
| 33 | ³ H-Ray Radiation Effects on an HfO ₂ -Based Resistive Memory Device. IEEE Nanotechnology Magazine, 2018, 17, 61-64. | 1.1 | 13 |
| 34 | Effect of Surface Scattering of Electrons on Ratios of Optical Absorption and Scattering to Extinction of Gold Nanoshell. Nanoscale Research Letters, 2018, 13, 299. | 3.1 | 13 |
| 35 | Realization of a Power-Efficient Transmitter Based on Integrated Artificial Neural Network. IEEE Access, 2018, 6, 68773-68781. | 2.6 | 10 |
| 36 | Smart electronic skin having gesture recognition function by LSTM neural network. Applied Physics Letters, 2018, 113, . | 1.5 | 20 |

| # | ARTICLE | IF | CITATIONS |
|----|--|------|-----------|
| 37 | Thickness effect of nickel oxide thin films on associated solution-processed write-once-read-many-times memory devices. <i>Applied Physics A: Materials Science and Processing</i> , 2018, 124, 1. | 1.1 | 12 |
| 38 | A Deformable and Highly Robust Ethyl Cellulose Transparent Conductor with a Scalable Silver Nanowires Bundle Micromesh. <i>Advanced Materials</i> , 2018, 30, e1802803. | 11.1 | 95 |
| 39 | Handwritten-Digit Recognition by Hybrid Convolutional Neural Network based on HfO ₂ Memristive Spiking-Neuron. <i>Scientific Reports</i> , 2018, 8, 12546. | 1.6 | 34 |
| 40 | Study of electrochromic characteristics in the near-infrared region of electrochromic devices based on solution-processed amorphous WO ₃ films. <i>Materials Science in Semiconductor Processing</i> , 2018, 88, 73-78. | 1.9 | 14 |
| 41 | Optical-reconfigurable carbon nanotube and indium-tin-oxide complementary thin-film transistor logic gates. <i>Nanoscale</i> , 2018, 10, 13122-13129. | 2.8 | 17 |
| 42 | Unlocking the potential of SnS ₂ : Transition metal catalyzed utilization of reversible conversion and alloying reactions. <i>Scientific Reports</i> , 2017, 7, 41015. | 1.6 | 26 |
| 43 | Direct Observation of Indium Conductive Filaments in Transparent, Flexible, and Transferable Resistive Switching Memory. <i>ACS Nano</i> , 2017, 11, 1712-1718. | 7.3 | 83 |
| 44 | Modeling of a selective solar absorber thin film structure based on double TiN _x O _y layers for concentrated solar power applications. <i>Solar Energy</i> , 2017, 142, 33-38. | 2.9 | 21 |
| 45 | A MoS ₂ -based coplanar neuron transistor for logic applications. <i>Nanotechnology</i> , 2017, 28, 214001. | 1.3 | 12 |
| 46 | W/Cu thin film infrared reflector for TiN _x O _y based selective solar absorber with high thermal stability. <i>Journal of Applied Physics</i> , 2017, 121, . | 1.1 | 6 |
| 47 | Nanoparticle-assisted Frenkel-Poole emission in two-terminal charging-controlled memory devices based on Si-rich silicon nitride thin films. <i>Applied Physics A: Materials Science and Processing</i> , 2017, 123, 1. | 1.1 | 1 |
| 48 | Synthesis of IGZO ink and study of ink-jet printed IGZO thin films with different Ga concentrations. <i>Solid-State Electronics</i> , 2017, 138, 108-112. | 0.8 | 5 |
| 49 | Influences of water molecules on the electronic properties of atomically thin molybdenum disulfide. <i>Applied Physics Letters</i> , 2017, 111, . | 1.5 | 7 |
| 50 | Investigation of localized surface plasmon resonance of TiN nanoparticles in TiN _x O _y thin films. <i>Optical Materials Express</i> , 2016, 6, 2422. | 1.6 | 20 |
| 51 | Amorphous Si-Based Resistive Switching Memories with Highly Reduced Electroforming Voltage and Enlarged Memory Window. <i>Advanced Electronic Materials</i> , 2016, 2, 1500370. | 2.6 | 23 |
| 52 | Hexagonal Boron Nitride Thin Film for Flexible Resistive Memory Applications. <i>Advanced Functional Materials</i> , 2016, 26, 2176-2184. | 7.8 | 167 |
| 53 | A light-stimulated synaptic transistor with synaptic plasticity and memory functions based on InGaZnOx/Al ₂ O ₃ thin film structure. <i>Journal of Applied Physics</i> , 2016, 119, . | 1.1 | 153 |
| 54 | Design of a High Performance Selective Solar Absorber with the Structure of SiO ₂ -TiO ₂ -TiN _x O _y -Cu. <i>ECS Journal of Solid State Science and Technology</i> , 2016, 5, N43-N47. | 0.9 | 9 |

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| 55 | Novel concepts in functional resistive switching memories. Journal of Materials Chemistry C, 2016, 4, 9637-9645. | 2.7 | 59 |
| 56 | Direct Observation of Conducting Filaments in Tungsten Oxide Based Transparent Resistive Switching Memory. ACS Applied Materials & Interfaces, 2016, 8, 27885-27891. | 4.0 | 80 |
| 57 | Resistive Switching in p-Type Nickel Oxide/n-Type Indium Gallium Zinc Oxide Thin Film Heterojunction Structure. ECS Journal of Solid State Science and Technology, 2016, 5, Q239-Q243. | 0.9 | 5 |
| 58 | Two dimensional layered Co _{0.85} Se nanosheets as a high-capacity anode for lithium-ion batteries. Nanoscale, 2016, 8, 14992-15000. | 2.8 | 90 |
| 59 | Resistive switching characteristics of RRAM devices based on spin-coated a-IGZO thin films and ink-jet printed Ag electrodes. , 2016, , . | | 1 |
| 60 | WS ₂ 3D graphene nano-architecture networks for high performance anode materials of lithium ion batteries. RSC Advances, 2016, 6, 107768-107775. | 1.7 | 29 |
| 61 | Ultrahigh Performance of Novel Capacitive Deionization Electrodes based on A Three-Dimensional Graphene Architecture with Nanopores. Scientific Reports, 2016, 6, 18966. | 1.6 | 105 |
| 62 | 3D hierarchical Co ₃ O ₄ @Co ₃ S ₄ nanoarrays as cathode materials for asymmetric pseudocapacitors. Journal of Materials Chemistry A, 2016, 4, 3287-3296. | 5.2 | 147 |
| 63 | Hydrothermally synthesized graphene and Fe ₃ O ₄ nanocomposites for high performance capacitive deionization. RSC Advances, 2016, 6, 11967-11972. | 1.7 | 52 |
| 64 | InGaZnO Thin-Film Transistors With Coplanar Control Gates for Single-Device Logic Applications. IEEE Transactions on Electron Devices, 2016, 63, 1383-1387. | 1.6 | 8 |
| 65 | Electronic and Optical Properties of Si and Ge Nanocrystals. Advances in Materials Science and Engineering, 2016, , 215-254. | 0.4 | 0 |
| 66 | Light Emission Properties of Si Nanocrystals Embedded in a Dielectric Matrix. Advances in Materials Science and Engineering, 2016, , 255-282. | 0.4 | 0 |
| 67 | Thickness Dependence of Optical Properties of Amorphous Indium Gallium Zinc Oxide Thin Films: Effects of Free-Electrons and Quantum Confinement. ECS Solid State Letters, 2015, 4, P29-P32. | 1.4 | 11 |
| 68 | Dielectric engineering of Ge nanocrystal/SiO ₂ nanocomposite thin films with Ge ion implantation: Modeling and measurement. Materials and Design, 2015, 83, 713-718. | 3.3 | 9 |
| 69 | Associative memory realized by a reconfigurable memristive Hopfield neural network. Nature Communications, 2015, 6, 7522. | 5.8 | 182 |
| 70 | Evolution of the localized surface plasmon resonance and electron confinement effect with the film thickness in ultrathin Au films. Journal of Nanoparticle Research, 2015, 17, 1. | 0.8 | 6 |
| 71 | Highly spectrum-selective ultraviolet photodetector based on p-NiO/n-IGZO thin film heterojunction structure. Optics Express, 2015, 23, 27683. | 1.7 | 37 |
| 72 | Study of Multilevel High-Resistance States in HfO _x -Based Resistive Switching Random Access Memory by Impedance Spectroscopy. IEEE Transactions on Electron Devices, 2015, 62, 2684-2688. | 1.6 | 11 |

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| 73 | Synaptic long-term potentiation realized in Pavlov's dog model based on a NiOx-based memristor. Journal of Applied Physics, 2014, 116, . | 1.1 | 52 |
| 74 | An Experimental Study of Lateral Charge Transfer in Silicon Nanocrystal Layer Embedded in SiO ₂ Thin Film. Nanoscience and Nanotechnology Letters, 2014, 6, 798-804. | 0.4 | 1 |
| 75 | Low dimension structures and devices for new generation photonic technology. , 2014, , . | | 0 |
| 76 | Influence of the Excess Al Content on Memory Behaviors of WORM Devices Based on Sputtered Al-Rich Aluminum Oxide Thin Films. Nanoscience and Nanotechnology Letters, 2014, 6, 845-848. | 0.4 | 0 |
| 77 | Influence of localized surface plasmon resonance and free electrons on the optical properties of ultrathin Au films: a study of the aggregation effect. Optics Express, 2014, 22, 5124. | 1.7 | 32 |
| 78 | A study on the evolution of dielectric function of ZnO thin films with decreasing film thickness. Journal of Applied Physics, 2014, 115, . | 1.1 | 27 |
| 79 | Lateral Conduction Switching in Sputtered Ni-Rich NiO Thin Films for Write-Once-Read-Many-Times Memory Applications. International Journal of Applied Ceramic Technology, 2014, 11, 732-737. | 1.1 | 1 |
| 80 | Evolution of dielectric function of Al-doped ZnO thin films with thermal annealing: effect of band gap expansion and free-electron absorption. Optics Express, 2014, 22, 23086. | 1.7 | 20 |
| 81 | Tunable long-distance light transportation along Au nanoparticle chains: promising for optical interconnect. Journal of Nanoparticle Research, 2014, 16, 1. | 0.8 | 0 |
| 82 | Realization of write-once-read-many-times memory device with O ₂ plasma-treated indium gallium zinc oxide thin film. Applied Physics Letters, 2014, 104, 033505. | 1.5 | 13 |
| 83 | Al Content-Dependent Resistive Switching in Al-Rich AlO _x N _y Thin Films. Nanoscience and Nanotechnology Letters, 2014, 6, 835-839. | 0.4 | 2 |
| 84 | Review of Nanostructured Resistive Switching Memristor and Its Applications. Nanoscience and Nanotechnology Letters, 2014, 6, 729-757. | 0.4 | 76 |
| 85 | <>A Special Issue on<> Nanoelectronics. Nanoscience and Nanotechnology Letters, 2014, 6, 727-728. | 0.4 | 0 |
| 86 | Development of optically transparent ZnS/poly(vinylpyrrolidone) nanocomposite films with high refractive indices and high Abbe numbers. Journal of Applied Polymer Science, 2013, 129, 1793-1798. | 1.3 | 14 |
| 87 | Effect of O ₂ plasma immersion on electrical properties and transistor performance of indium gallium zinc oxide thin films. Thin Solid Films, 2013, 545, 533-536. | 0.8 | 19 |
| 88 | Magnetron Sputtered Ni-Rich Nickel Oxide Nano-Films for Resistive Switching Memory Applications. International Journal of Applied Ceramic Technology, 2013, 10, 20-25. | 1.1 | 13 |
| 89 | Emulating the paired-pulse facilitation of a biological synapse with a NiOx-based memristor. Applied Physics Letters, 2013, 102, . | 1.5 | 119 |
| 90 | Electroluminescence from SiO ₂ Thin Film Embedded with Self-Assembled Gold Nanoparticles. Nanoscience and Nanotechnology Letters, 2013, 5, 857-860. | 0.4 | 2 |

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| 91 | Effects of free electrons and quantum confinement in ultrathin ZnO films: a comparison between undoped and Al-doped ZnO. Optics Express, 2013, 21, 14131. | 1.7 | 35 |
| 92 | Effect of Exposure to Ultraviolet-Activated Oxygen on the Electrical Characteristics of Amorphous Indium Gallium Zinc Oxide Thin Film Transistors. ECS Solid State Letters, 2013, 2, Q21-Q24. | 1.4 | 28 |
| 93 | Recovery from ultraviolet-induced threshold voltage shift in indium gallium zinc oxide thin film transistors by positive gate bias. Applied Physics Letters, 2013, 103, . | 1.5 | 10 |
| 94 | Design of an electronic synapse with spike time dependent plasticity based on resistive memory device. Journal of Applied Physics, 2013, 113, . | 1.1 | 14 |
| 95 | Si nanocrystal-based triple-layer anti-reflection coating for Si solar cells. Journal of Applied Physics, 2013, 114, 053109. | 1.1 | 3 |
| 96 | Ink-jet printed In-Ga-Zn oxide nonvolatile TFT memory utilizing silicon nanocrystals embedded in SiO ₂ gate dielectric. , 2013, , . | | 1 |
| 97 | Emulating the Ebbinghaus forgetting curve of the human brain with a NiO-based memristor. Applied Physics Letters, 2013, 103, . | 1.5 | 90 |
| 98 | Temperature-Dependent Charge Transport in Al/Al Nanocrystal Embedded Al ₂ O ₃ Nanocomposite/p-Si Diodes. ECS Solid State Letters, 2012, 1, Q4-Q7. | 1.4 | 11 |
| 99 | Modeling of lateral charge transfer in Si nanocrystals in SiO ₂ thin film. Journal of Applied Physics, 2012, 111, 073707. | 1.1 | 0 |
| 100 | Influence of SiO ₂ Layer on the Dielectric Function of Gold Nanoparticles on Si Substrate. Electrochemical and Solid-State Letters, 2012, 15, K5. | 2.2 | 2 |
| 101 | Realization of transient memory-loss with NiO-based resistive switching device. Applied Physics A: Materials Science and Processing, 2012, 109, 349-352. | 1.1 | 3 |
| 102 | Size-suppressed dielectrics of Ge nanocrystals: skin-deep quantum entrapment. Nanoscale, 2012, 4, 1308. | 2.8 | 7 |
| 103 | Wavelength tunable electroluminescence from randomly assembled n-CdS _x Se _{1-x} nanowires/p-SiC heterojunction. Nanoscale, 2012, 4, 1467-1470. | 2.8 | 7 |
| 104 | Conduction mechanisms at low- and high-resistance states in aluminum/anodic aluminum oxide/aluminum thin film structure. Journal of Applied Physics, 2012, 112, . | 1.1 | 35 |
| 105 | Resistive Switching Behavior of Partially Anodized Aluminum Thin Film at Elevated Temperatures. IEEE Transactions on Electron Devices, 2012, 59, 2363-2367. | 1.6 | 15 |
| 106 | Controlled electroluminescence of n-ZnMgO/p-GaN light-emitting diodes. Applied Physics Letters, 2012, 101, . | 1.5 | 13 |
| 107 | Strong green emission in ZnO films after H ₂ surface treatment. Journal Physics D: Applied Physics, 2012, 45, 185102. | 1.3 | 13 |
| 108 | A quantitative modeling of the contributions of localized surface plasmon resonance and interband transitions to absorbance of gold nanoparticles. Journal of Nanoparticle Research, 2012, 14, 1. | 0.8 | 14 |

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| 109 | Flexible Write-Once-Read-Many-Times Memory Device Based on a Nickel Oxide Thin Film. IEEE Transactions on Electron Devices, 2012, 59, 858-862. | 1.6 | 16 |
| 110 | Effect of Heat Diffusion During State Transitions in Resistive Switching Memory Device Based on Nickel-Rich Nickel Oxide Film. IEEE Transactions on Electron Devices, 2012, 59, 1558-1562. | 1.6 | 7 |
| 111 | Flexible Nanoscale Memory Device Based on Resistive Switching in Nickel Oxide Thin Film. Nanoscience and Nanotechnology Letters, 2012, 4, 940-943. | 0.4 | 4 |
| 112 | Optical Properties of Gold Nanoparticles on Heavily-Doped Si Substrate Synthesized with an Electrochemical Process. Journal of the Electrochemical Society, 2011, 158, K152. | 1.3 | 6 |
| 113 | Ultraviolet Random Lasing Action from Highly Disordered n-AlN/p-GaN Heterojunction. ACS Applied Materials & Interfaces, 2011, 3, 1726-1730. | 4.0 | 13 |
| 114 | Laterally-current-injected light-emitting diodes based on nanocrystalline-Si/SiO ₂ superlattice. Optics Express, 2011, 19, 2729. | 1.7 | 17 |
| 115 | Profile Uniformity of Overlapped Oxide Dots Induced by Atomic Force Microscopy: (Journal of) Tj ETQq1 1 0.784314 rgBT /Overlock 101 Nanotechnology, 2011, 11, 899-899. | 0.9 | 0 |
| 116 | Bandgap expansion and dielectric suppression of self-assembled Ge nanocrystals. Journal of Applied Physics, 2011, 109, . | 1.1 | 15 |
| 117 | Annealing-Induced Changes in Electrical Characteristics of Al/Al-Rich $\text{Al}_2\text{O}_3/\text{Si}$ Diodes. IEEE Transactions on Electron Devices, 2011, 58, 33-38. | 1.6 | 3 |
| 118 | Two-Terminal Write-Once-Read-Many-Times Memory Device Based on Charging-Controlled Current Modulation in Al/Al-Rich $\text{Al}_2\text{O}_3/\text{p-Si}$ Diode. IEEE Transactions on Electron Devices, 2011, 58, 960-965. | 1.6 | 12 |
| 119 | Influence of implantation dose on electroluminescence from $\hat{\text{A}}\text{Si}$ -implanted silicon nitride thin films. Applied Physics A: Materials Science and Processing, 2011, 104, 239-245. | 1.1 | 12 |
| 120 | Self-learning ability realized with a resistive switching device based on a Ni-rich nickel oxide thin film. Applied Physics A: Materials Science and Processing, 2011, 105, 855-860. | 1.1 | 9 |
| 121 | Temperature dependence of current transport in Al/Al ₂ O ₃ nanocomposite thin films. Journal of Applied Physics, 2011, 110, 096108. | 1.1 | 3 |
| 122 | Competition of Resistive-Switching Mechanisms in Nickel-Rich Nickel Oxide Thin Films. Electrochemical and Solid-State Letters, 2011, 14, H400. | 2.2 | 4 |
| 123 | Temperature Dependence of Resistive Switching in Aluminum/Anodized Aluminum Film Structure. Nanoscience and Nanotechnology Letters, 2011, 3, 222-225. | 0.4 | 3 |
| 124 | Resistive Switching in a Ni-Rich Nickel Oxide Thin Film. Nanoscience and Nanotechnology Letters, 2011, 3, 267-271. | 0.4 | 1 |
| 125 | Profile Uniformity of Overlapped Oxide Dots Induced by Atomic Force Microscopy. Journal of Nanoscience and Nanotechnology, 2010, 10, 4390-4399. | 0.9 | 4 |
| 126 | A Two-Terminal Write-Once-Read-Many-Times-Memory Device Based on an Aluminum Nitride Thin Film Containing Al Nanocrystals. Journal of Nanoscience and Nanotechnology, 2010, 10, 5796-5799. | 0.9 | 4 |

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| 127 | Si-Based Light-Emitting Structure Synthesized with Low-Energy Ion Implantation at a Low Dosage. Journal of Nanoscience and Nanotechnology, 2010, 10, 595-598. | 0.9 | 0 |
| 128 | Charging Effect of Aluminum Nitride Thin Films Containing Al Nanocrystals. Journal of Nanoscience and Nanotechnology, 2010, 10, 599-603. | 0.9 | 6 |
| 129 | Charge Storage Behaviors of Ge Nanocrystals Embedded in SiO ₂ for the Application in Non-Volatile Memory Devices. Journal of Nanoscience and Nanotechnology, 2010, 10, 4517-4521. | 0.9 | 5 |
| 130 | Improvement of Negative Bias Temperature Instability by Stress Proximity Technique. IEEE Transactions on Electron Devices, 2010, 57, 238-243. | 1.6 | 5 |
| 131 | Electroluminescence of as-sputtered silicon-rich SiO _x films. Vacuum, 2010, 84, 1043-1048. | 1.6 | 18 |
| 132 | Physics of electron mobility independent of channel orientation in n-channel transistors based on (100) silicon wafers and its experimental verification. Applied Physics Letters, 2010, 97, 133508. | 1.5 | 1 |
| 133 | Scratch properties of nickel thin films using atomic force microscopy. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2010, 28, 202-210. | 0.6 | 28 |
| 134 | Tunable Surface Plasmon Resonance of Gold Nanoparticles Self-Assembled on Fused Silica Substrate. Electrochemical and Solid-State Letters, 2010, 13, K96. | 2.2 | 10 |
| 135 | Comparison of Charge Storage Behavior of Electrons and Holes in a Continuous Ge Nanocrystal Layer. Nanoscience and Nanotechnology Letters, 2010, 2, 7-10. | 0.4 | 4 |
| 136 | Charging Effect on Conductance of Magnetron Sputtered Si Nanocrystals Embedded SiO ₂ Films. Nanoscience and Nanotechnology Letters, 2010, 2, 226-230. | 0.4 | 1 |
| 137 | The charge trapping and memory effect in SiO ₂ thin films containing Ge nanocrystals. Journal Physics D: Applied Physics, 2010, 43, 015102. | 1.3 | 10 |
| 138 | Charging effect on electroluminescence performance of nc-Si/a-SiO ₂ films. Journal of Applied Physics, 2010, 107, 043709. | 1.1 | 2 |
| 139 | Microstructure of Magnetron Sputtered Amorphous SiO _x Films: Formation of Amorphous Si Core-Shell Nanoclusters. Journal of Physical Chemistry C, 2010, 114, 2414-2420. | 1.5 | 45 |
| 140 | Collective Excitations and Dielectric Function of Self-Assembled Gold Nanoparticles on a Silicon Substrate. Electrochemical and Solid-State Letters, 2010, 13, K39. | 2.2 | 6 |
| 141 | Electroluminescence from n-In ₂ O ₃ :Sn randomly assembled nanorods/p-SiC heterojunction. Optics Express, 2010, 18, 15585. | 1.7 | 11 |
| 142 | Electrically tunable white-color electroluminescence from Si-implanted silicon nitride thin film. Optics Express, 2010, 18, 20439. | 1.7 | 28 |
| 143 | Split of surface plasmon resonance of gold nanoparticles on silicon substrate: a study of dielectric functions. Optics Express, 2010, 18, 21926. | 1.7 | 24 |
| 144 | Static dielectric constant of Al nanocrystal/Al ₂ O ₃ nanocomposite thin films determined by the capacitance-voltage reconstruction technique. Applied Physics Letters, 2010, 96, 173110. | 1.5 | 6 |

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| 145 | Thickness effect on the band gap and optical properties of germanium thin films. Journal of Applied Physics, 2010, 107, . | 1.1 | 117 |
| 146 | Evolution of electroluminescence from multiple Si-implanted silicon nitride films with thermal annealing. Journal of Applied Physics, 2009, 105, 123101. | 1.1 | 16 |
| 147 | Parasitic memory effect induced by high erasing pulses in metal-oxide-semiconductor field-effect transistor device containing silicon nanocrystals. Journal of Applied Physics, 2009, 105, 114501. | 1.1 | 1 |
| 148 | High temperature excitonic lasing characteristics of randomly assembled SnO ₂ nanowires. Applied Physics Letters, 2009, 95, . | 1.5 | 16 |
| 149 | Capacitance switching in SiO ₂ thin film embedded with Ge nanocrystals caused by ultraviolet illumination. Applied Physics Letters, 2009, 95, 091111. | 1.5 | 1 |
| 150 | Strong violet and green-yellow electroluminescence from silicon nitride thin films multiply implanted with Si ions. Applied Physics Letters, 2009, 94, . | 1.5 | 35 |
| 151 | Anomalous capacitance-voltage characteristics of Al/Al-rich Al ₂ O ₃ /p-Si capacitors and their reconstruction. Applied Physics Letters, 2009, 94, 243106. | 1.5 | 4 |
| 152 | Current conduction in Al/Si nanocrystal embedded SiO ₂ /p-Si diodes with various distributions of Si nanocrystals in the oxide. Journal of Applied Physics, 2009, 106, 013718. | 1.1 | 7 |
| 153 | Large magnetic moment obtained in Cu-doped ZnO nanoclusters. , 2009, , . | | 0 |
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